

U.S. Patent Application Serial No. 10/699,832  
Amendment filed December 8, 2006  
Reply to OA dated August 8, 2006

**AMENDMENTS TO THE CLAIMS:**

Please cancel claims 5, 10 and 11 without prejudice or disclaimer, and amend claims 1, 3 and 4, as follows. This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

Claim 1 (Currently Amended): A substrate for an electronic-optical united device ~~used for fabricating~~ being a component of an electronic-optical united device mixedly incorporating an electronic device such as an LSI and an optical device such as an LED and a laser diode, comprising a monocrystalline silicon substrate being an SOI substrate including:

~~one area having at least one layer, wherein none of the layers of said one area is metamorphosed formed with the electronic device; and~~

another area formed with the electronic device, comprising:

a layer of silicon carbide metamorphosed by locally carbonizing the corresponding area in the monocrystalline silicon SOI substrate; and

a layer of monocrystalline gallium nitride grown on said layer of silicon carbide.

Claim 2 (Canceled).

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Claim 3 (Currently Amended): A substrate for an electronic-optical united device according to claim 1, said one area further comprising:

a layer of silicon nitride formed on the ~~monocrystalline silicon~~ SOI substrate.

Claim 4 (Currently Amended): A substrate for an electronic-optical united device according to claim 1, said one area further comprising:

a layer of silicon oxide formed on the ~~monocrystalline silicon~~ SOI substrate.

Claims 5-11 (Canceled).

Claim 12 (Previously Presented): A substrate for an electronic-optical united device according to claim 3, said one area further comprising:

a layer of polycrystalline gallium nitride grown on the layer of silicon nitride.

Claim 13 (Previously Presented): A substrate for an electronic-optical united device according to claim 4, said one area further comprising:

a layer of polycrystalline gallium nitride grown on the layer of silicon oxide.